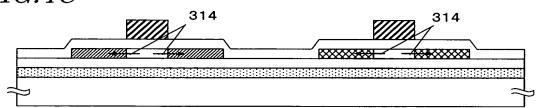
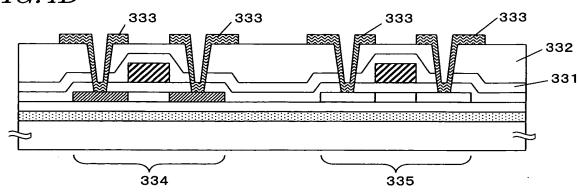


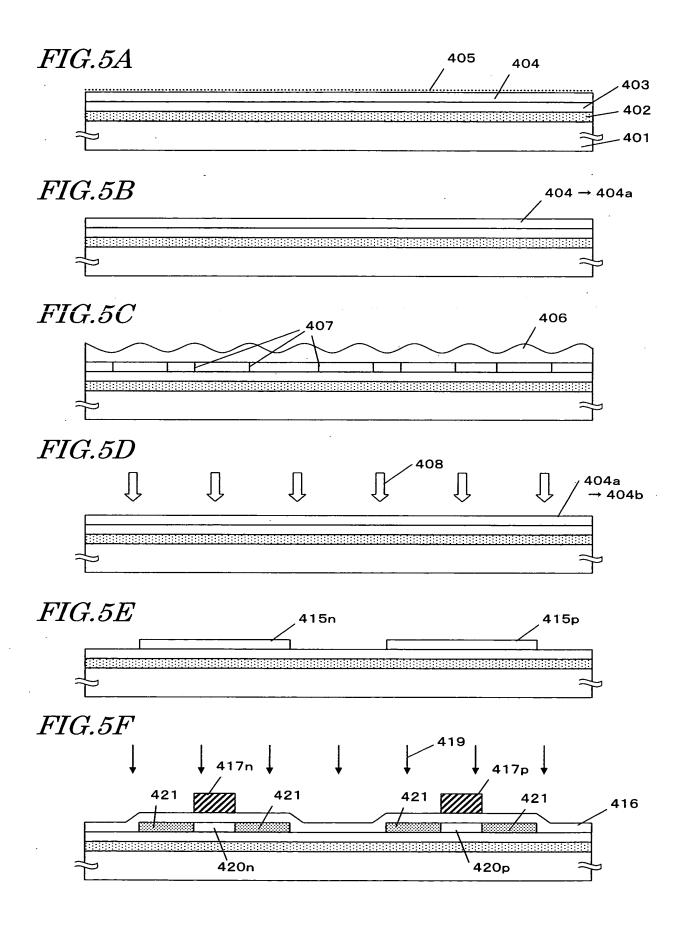
FIG.4C

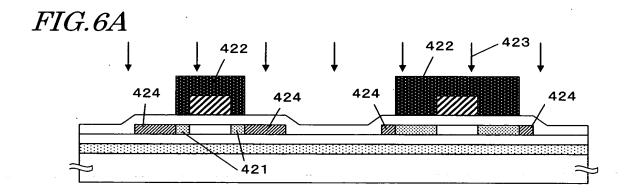


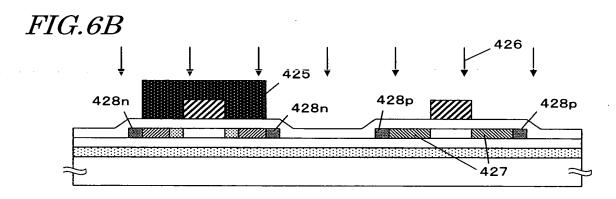
320p

FIG.4D

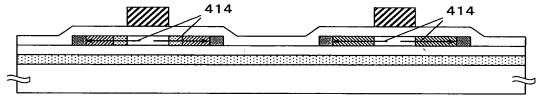


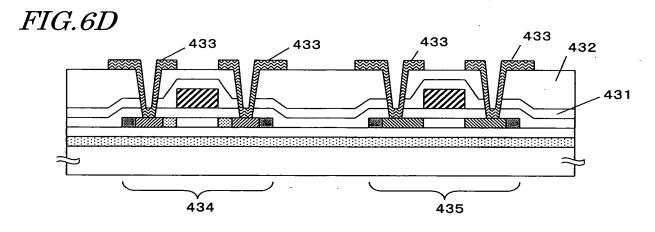


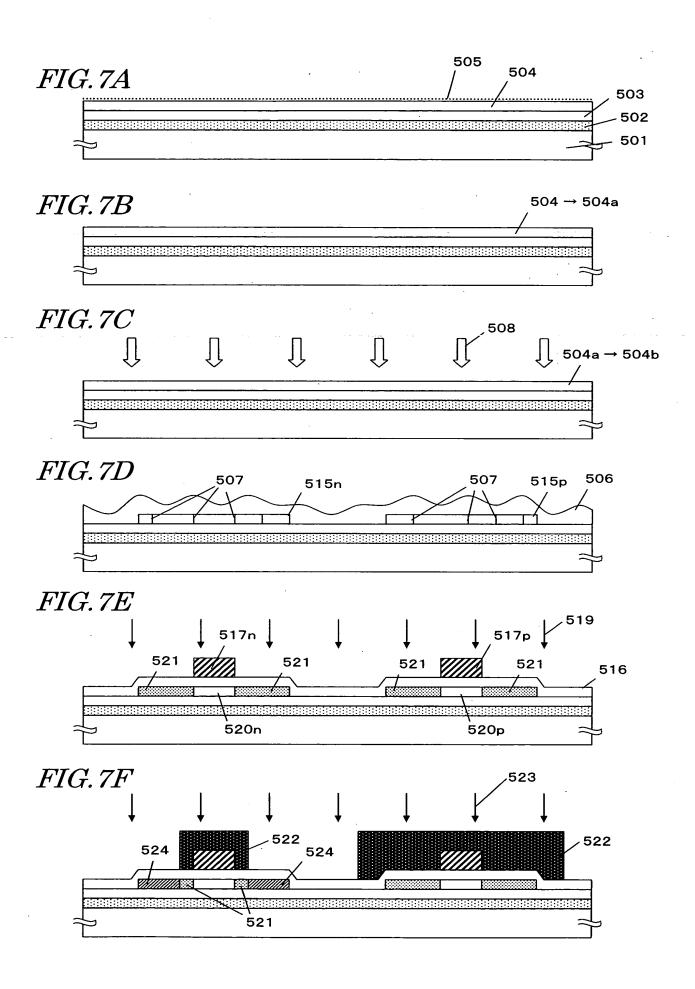


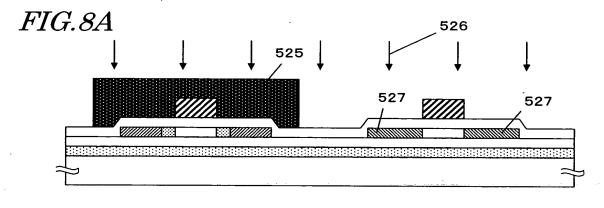












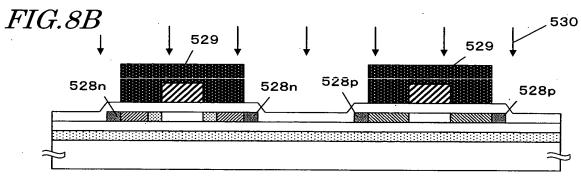
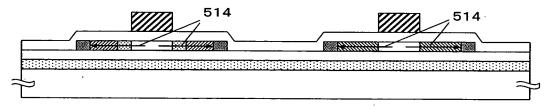
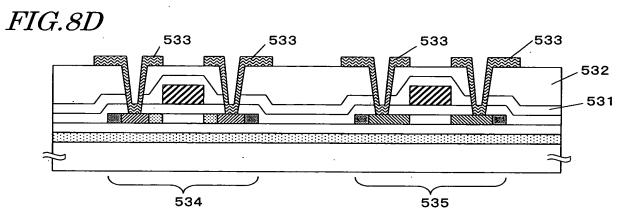
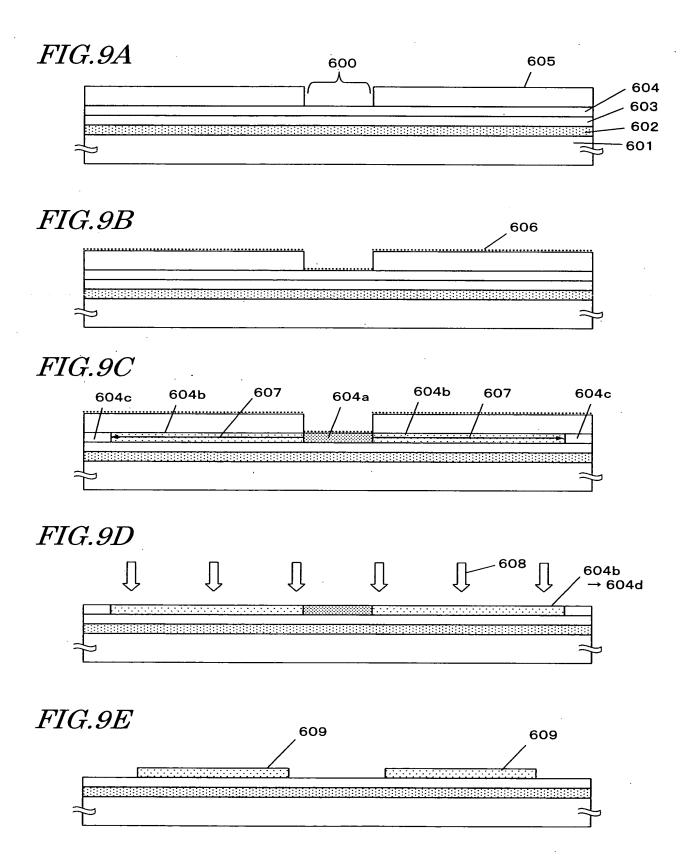
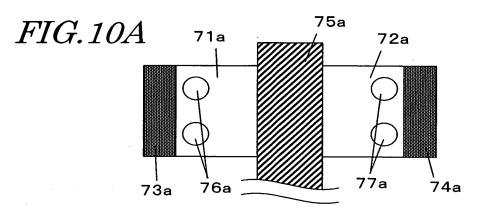


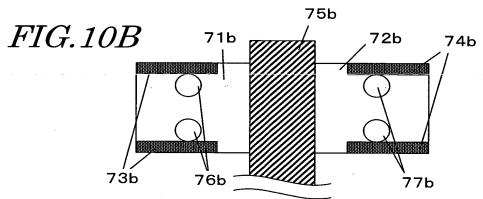
FIG.8C

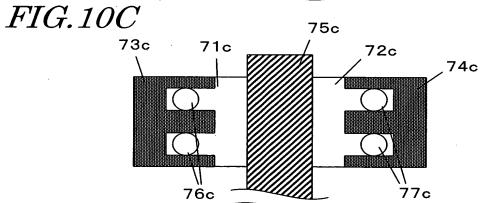


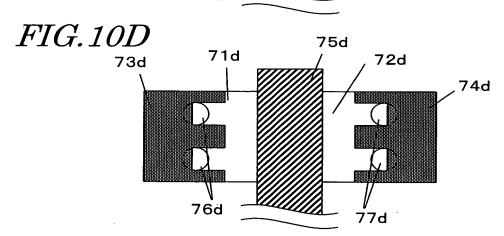


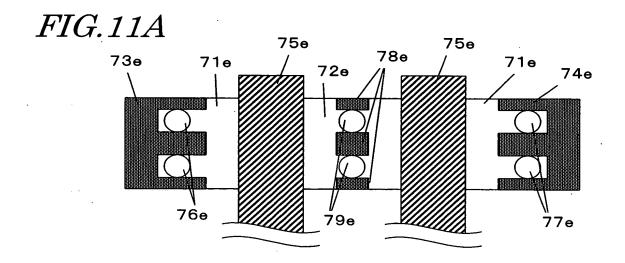


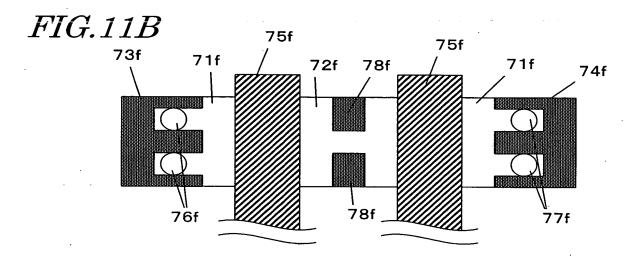












FIC 10A	80 Source Driving Circuit (Source Driver)
FIG.12A	80a Shift Register
	80b Buffer
	80c Sampling Circuit
Gate Driving Circuit & (Gate Driver) Shift Register & Barfer & Buffer & Company & Comp	81 Pixel Section

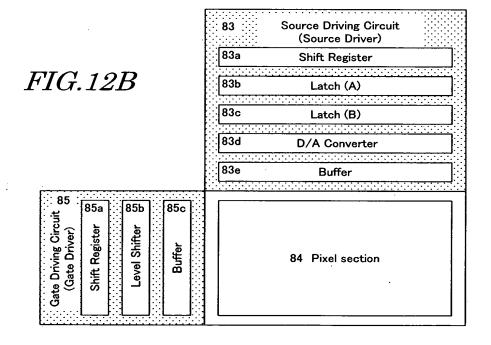
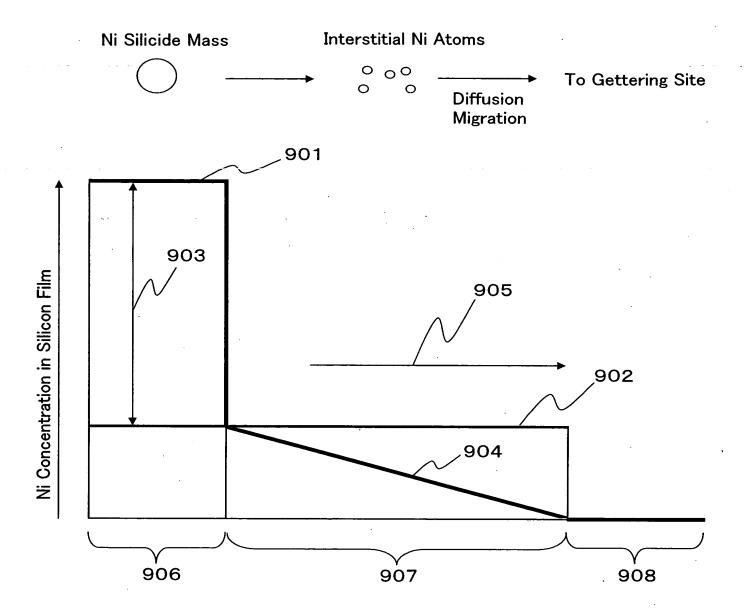
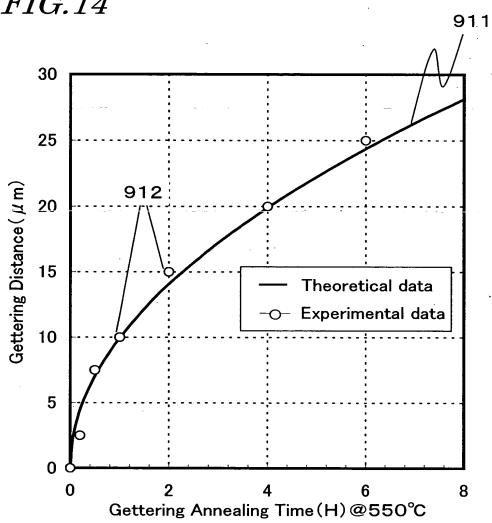


FIG.13







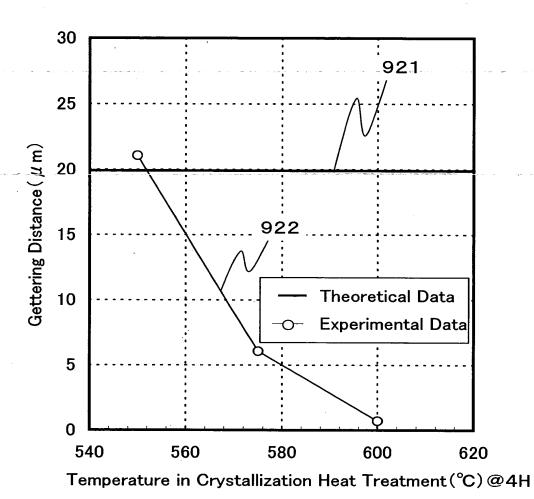
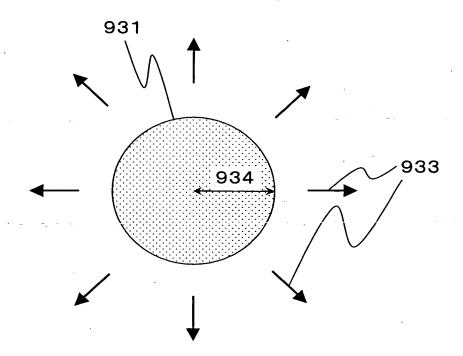
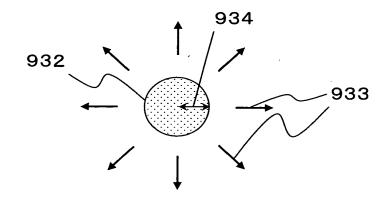


FIG.16Temperature in Crystallization Heat Treatment 50 μ m

FIG.17





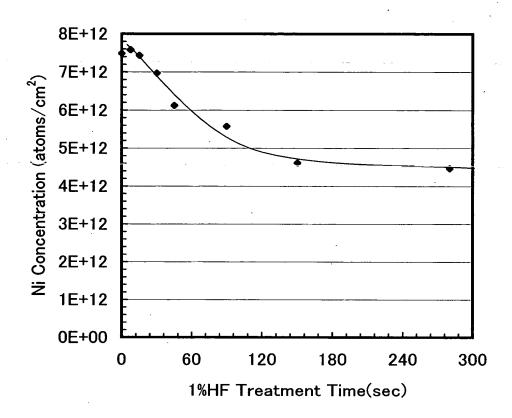
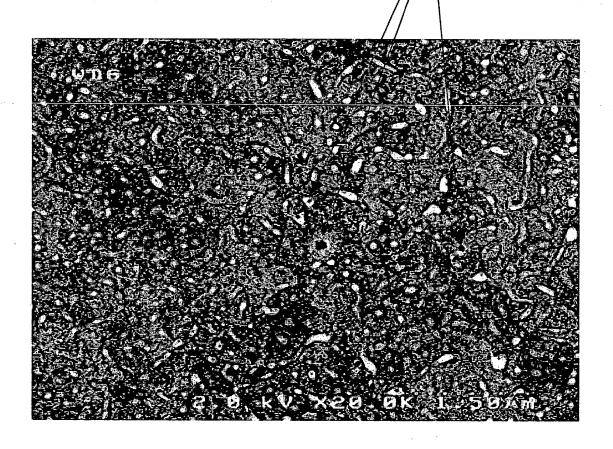


FIG.19

Minute Holes Formed After Removing Ni Silicide Masses



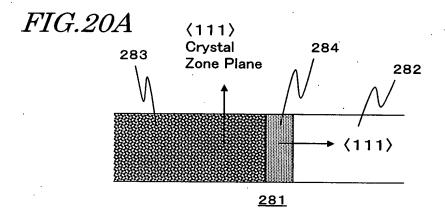


FIG.20B

